Printe, Dages - 4

Roll No.:....

# C028611(028)

# B. Tech. (Sixth Semester) Examination, April-May 2022

AICTE (New Scheme)

(Electronics & Telecommunication Branch)

### VLSI DESIGN

Time Allowed: Three hours

Maximum Marks: 100

Minimum Pass Marks: 35

Note: Part (a) of each question is compulsory and it carries 4 marks. Attempt any two part from (b), (c) and (d) of each question. Part (b), (c) and (d) carry 8 marks each.

## Unit-I

- 1. (a) What is Transmission gate? Draw the Exclusive-OR gate using Transmission gates.
  - (b) Draw the CMOS schematic of 2-i/p NAND & NOR Gate and explain their operation.

C028611(028)

PTO

(c) Design a CMOS circuit for the OAI expression

$$h = \overline{(a+b)\cdot(a+c)\cdot(b+d)}$$

Use the smallest number of transistors in your design.

- (d) An inverter uses FETs with  $\beta_n = 2 \cdot 1 \text{ mA/V}^2$  and  $\beta_p = 1 \cdot 8 \text{ mA/V}^2$ . The threshold voltages are given as  $V_{Tn} = 0 \cdot 60 \text{ V}$  and  $V_{Tp} = -0 \cdot 70 \text{ V}$  and the power supply has a value of  $V_{DD} = 5 \text{ V}$ . The parasitic FET capacitance at the output node is estimated to be  $C_{\text{FET}} = 74 \text{ fF}$ .
  - (i) Find the midpoint voltage  $V_{M}$
  - (ii) Find the value of  $R_n$  and  $R_p$
  - (iii) Calculate the rise and fall times at the output when  $C_L = 0$ .
  - (iv) Calculate the rise and fall times when an external load of value  $C_L = 115~{\rm fF}$  is connected to the output.

## Unit-II

2. (a) Define Lithography.

- (b) Describe the various steps involved in fabrication process of CMOS using *n*-well process.
- (c) Discuss Lamda-based design rules for layout designing in brief.
- (d) Draw the stick diagram and Layout for two-input CMOS NAND gate. Align the transistors horizontally.

### Unit-III

- 3. (a) Draw the schematic of RS Flip-Flop.
  - (b) Design CMOS Schematic of full adder circuit using minimum number of transistors.
  - (c) Explain the working of  $4 \times 4$  NOR-ROM and  $4 \times 4$  NAND-ROM with their schematic only.
  - (d) Draw the Schematic of 6-T DRAM and explain the working principle.

## **Unit-IV**

- 4. (a) Give the comparisons between CPLD and FPGA.
  - (b) (i) Consider the function  $f(x_1, x_2, x_3) = \sum m$ (2, 3, 4, 6, 7). Show how it can be realized

 $b_{ij}$ 

using two two-input LUTs. Give the truth table implemented in each LUT. You do not need to show the wires in the FPGA.

- (ii) Write the VHDL codes for 8\*1 Mux using With-Select statement.
- (c) Write VHDL code for Full adder using Structural Modeling styles.
- (d) Write the VHDL codes for 8-line to 3-line Encoder using CASE statement.

## **Unit-V**

- 5. (a) What are the differences between signals and variables?
  - (b) What is FSM? Differentiate Mealy and Moore FSM.
  - (c) Write VHDL Code for T-Flip-Flop using Behavioral modeling styles.
  - (d) Write the VHDL codes for Synchronous BCD counter.